

L Number	Hits	Search Text	DB	Time stamp
1	339	(438/704).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT	2004/05/14 15:22
2	679	(349/187).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT	2004/05/14 15:23
4	552	(216/97).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT	2004/05/14 15:26
5	855	(216/99).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT	2004/05/14 15:26
3	209	(216/80).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT	2004/05/14 15:27
7	39	((216/97).CCLS.) ((216/99).CCLS.) ((216/80).CCLS.)) and (LCD liquid adj crystal)	USPAT; US-PPGPUB; EPO; JPO; DERWENT	2004/05/14 15:27
8	132	349/\$.ccls. and etch\$3 same substrate and (dry plasma)adj2 etch\$3 RIE CDE half adj ash) and (planarize planarization planarized cleaning) and (process method).ti. (216/23).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT	2004/05/14 15:28
9	152		USPAT; US-PPGPUB; EPO; JPO; DERWENT	2004/05/14 15:28
10	1421	(349/158).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT	2004/05/14 15:30